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Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	12	(("6365963B1") or ("6038136") or ("5697148") or ("6121686") or ("6242279B1") or ("6130477") or ("6077724") or ("6024275")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/28 09:56
S2	0	S1 and (substrate or wafer or semiconductor) and connect\$4 and ("IC" or "integrated circuit") and resin	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/07/28 09:57
S3	43381	(substrate or wafer or semiconductor) and connect\$4 and ("IC" or "integrated circuit") and resin	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/28 09:58
S4	16355	(substrate or wafer or semiconductor) and connect\$4 and ("IC" or "integrated circuit") and resin and package	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/28 09:58
S5	347	(substrate or wafer or semiconductor) and connect\$4 and ("IC" or "integrated circuit") and resin and package and gas and pressure and (liquid near4 resin)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/28 09:59
S6	93	(substrate or wafer or semiconductor) and connect\$4 and ("IC" or "integrated circuit") and resin and package and gas and pressure and (liquid near4 resin) and "flip chip"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/28 09:59
S7	1	(substrate or wafer or semiconductor) and connect\$4 and ("IC" or "integrated circuit") and resin and package and gas and pressure and (liquid near4 resin) and "flip chip" and (contact or pad) and laminar	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/28 10:01
S9	1	(substrate or wafer or semiconductor) and connect\$4 and ("IC" or "integrated circuit") and resin and package and gas and pressure and (liquid near4 resin) and "flip chip" and (contact or pad) and laminar and hole	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/28 10:02

S10	84	(substrate or wafer or semiconductor) and connect\$4 and ("IC" or "integrated circuit") and resin and package and gas and pressure and (liquid near4 resin) and "flip chip" and (contact or pad) and hole\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 10:51
S11	1604213	("IC" or "integrated circuit")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 10:51
S12	1239	("IC" or "integrated circuit") and (substrate or wafer or semiconductor) and connect\$4 and encas\$4 and resin	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 10:54
S13	996	("IC" or "integrated circuit") and (substrate or wafer or semiconductor) and connect\$4 and encas\$4 and resin and (hole or via or trench)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 10:56
S14	1	("IC" or "integrated circuit") and (substrate or wafer or semiconductor) and connect\$4 and encas\$4 and resin and (hole or via or trench) and box and gas and pressure and volume and (solder near ball) and (flip near4 chip) and wire and laminar	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON .	2006/08/01 11:00
S15	1	("IC" or "integrated circuit") and (substrate or wafer or semiconductor) and connect\$4 and encas\$4 and resin and (hole or via or trench) and box and gas and pressure and volume and (solder near ball) and (flip near4 chip) and wire	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON .	2006/08/01 11:00
S16	16	("IC" or "integrated circuit") and (substrate or wafer or semiconductor) and connect\$4 and encas\$4 and resin and (hole or via or trench) and gas and pressure and volume and (solder near ball) and (flip near4 chip) and wire	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 11:31

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S17	1	("IC" or "integrated circuit") and (substrate or wafer or semiconductor) and connect\$4 and encas\$4 and resin and (hole or via or trench) and gas and pressure and volume and (solder near ball) and (flip near4 chip) and wire and laminar	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 11:01
S18	669	("IC" or "integrated circuit") same (substrate or wafer or semiconductor) and connect\$4 and encas\$4 and resin and (hole or via or trench)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 11:31
S19	149	("IC" or "integrated circuit") same (substrate or wafer or semiconductor) and connect\$4 and encas\$4 and resin and (hole or via or trench) and (flip near chip)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 11:32
S20	2	("IC" or "integrated circuit") same (substrate or wafer or semiconductor) and connect\$4 and encas\$4 and resin and (hole or via or trench) and (flip near chip) and (laminar near8 substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 11:33
S21	149	("IC" or "integrated circuit") same (substrate or wafer or semiconductor) and connect\$4 and encas\$4 and resin and (hole or via or trench) and (flip near chip)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 13:05
S22	22	("IC" or "integrated circuit") same (substrate or wafer or semiconductor) and connect\$4 and encas\$4 and (liquid near4 resin) and (hole or via or trench) and (flip near chip)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 13:46
S23	26	("IC" or "integrated circuit") same (substrate or wafer or semiconductor) and connect\$4 and encas\$4 and (liquid near4 resin) and (hole or open\$3) and (flip near chip)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 13:47
S24	25	("IC" or "integrated circuit") near8 (substrate or wafer or semiconductor) and connect\$4 and encas\$4 and (liquid near4 resin) and (hole or open\$3) and (flip near chip)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 13:51

S25	4	("IC" or "integrated circuit") near8 (substrate or wafer or semiconductor) and connect\$4 and encas\$4 and (liquid near4 resin) and (hole or open\$3) and (flip near chip) and gas	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 14:09
S26	3	("integrated circuit" near8 substrate) and connect\$4 and encas\$4 and (liquid near4 resin) and (hole or open\$3) and (flip near chip) and gas	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 14:10
S27	21	("integrated circuit" near8 substrate) and connect\$4 and encas\$4 and (liquid near4 resin) and (hole or open\$3) and (flip near chip)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/02 10:44
S28	2777	encas\$4 near8 resin	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 14:13
S29	406	(encas\$4 near8 resin) and (liquid near4 resin)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 14:13
S30	65	(encas\$4 near8 resin) and (liquid near4 resin) and ("IC" or "integrated circuit")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 14:14
S31	38	(encas\$4 near8 resin) and (liquid near4 resin) and ("IC" or "integrated circuit") and (substrate or semiconductor or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 14:14
S32	16	(encas\$4 near8 resin) and (liquid near4 resin) and ("IC" or ."integrated circuit") and (substrate or semiconductor or wafer) and (flip near4 chip)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 14:15

S33	1	(encas\$4 near8 resin) and (liquid near4 resin) and ("IC" or "integrated circuit") and (substrate or semiconductor or wafer) and (flip near4 chip) and gas and solder	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 14:19
S34	11	(encas\$4 near8 resin) and (liquid near4 resin) and ("IC" or "integrated circuit") and (substrate or semiconductor or wafer) and (flip near4 chip) and solder	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR ·	ON	2006/08/01 14:20
S35	8	(encas\$4 near8 resin) and (liquid near4 resin) and ("IC" or "integrated circuit") and (substrate or semiconductor or wafer) and (flip near4 chip) and solder and (hole\$2 or open\$3 or via)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 14:20
S36	12	(("6365963B1") or ("6038136") or ("5697148") or ("6121686") or ("6242279B1") or ("6130477") or ("6077724") or ("6024275")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/02 07:22
S37	1	(substrate near8 hole\$2) and encas\$4 and resin and box and gas and mold\$4 and pressure and volume and (laminar near8 substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/02 10:48
S38	1	(substrate near8 hole\$2) and encas\$4 and resin and pressure and volume and (laminar near8 substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/02 10:48
S39	13	(substrate near8 hole\$2) and encas\$4 and resin and (laminar near8 substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/02 10:48
S40	6	(substrate near8 hole\$2) and encas\$4 and resin and (laminar near8 substrate) and box	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/02 10:49

S41	6	(substrate near8 hole\$2) and encas\$4 and resin and (laminar near8 substrate) and box and gas	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/02 10:49
S42	6	(substrate near8 hole\$2) and encas\$4 and resin and (laminar near8 substrate) and box and gas and pressure	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/02 10:49
S43	6	(substrate near8 hole\$2) and encas\$4 and resin and (laminar near8 substrate) and box and gas and pressure and (solder near4 ball)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/02 10:49
S44	1	(substrate near8 hole\$2) and encas\$4 and resin and (laminar near8 substrate) and box and gas and pressure and (solder near4 ball) and (flip near4 chip)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/02 10:50
S45	6	(substrate near8 hole\$2) and encas\$4 and resin and (laminar near8 substrate) and box and gas and pressure and (solder near4 ball) and (recess or indent)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/02 10:50